

F1622

16,384 x 4-Bit Static RAM

Memory and High Speed Logic

Description

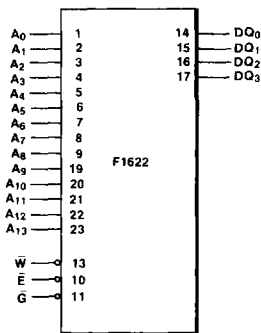
The F1622 is a 65,536-bit fully static asynchronous random access memory, organized as 16,384 words by 4-bits per word, using high-performance CMOS technology. The F1622 is based on an advanced isoplanar oxide isolation process: fully-implanted CMOS technology with sub-2 micron design rules and high-performance tantalum silicide gate electrodes. The high-density NMOS memory array and the CMOS peripheral circuits provide fast access time plus low active and standby power.

- **Single -5V Operation ($\pm 10\%$)**
- **Fully Static: No Clock or Timing Strobe Required**
- **Fast Access Time:**
 - Commercial: 25 ns/35 ns (Maximum)
 - Military: 35 ns/45 ns (Maximum)
- **Available in Commercial (0°C to +70°C) or Military (-55°C to +125°C) Versions**
- **Low Power Dissipation:**
 - 90/70 mA Maximum (Active)
 - 20/15 mA Maximum (Standby — TTL Input Levels)
 - 2 mA Maximum (Standby — CMOS Input Levels)
- **Directly TTL Compatible — All Inputs and Outputs**
- **Available in a 24-Pin DIP or 28-Terminal LCC**
- **Polyimide Die Coat for Alpha Immunity**

Pin Names

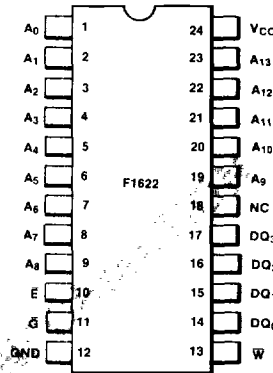
A ₀ -A ₁₃	Address Inputs
\bar{E}	Chip Enable
\bar{W}	Write Enable
\bar{G}	Output Enable
DQ ₀ -DQ ₃	Data Inputs/Outputs
V _{CC}	Power (5.0V)
GND	Ground (0V)
NC	No Connection

Logic Symbol

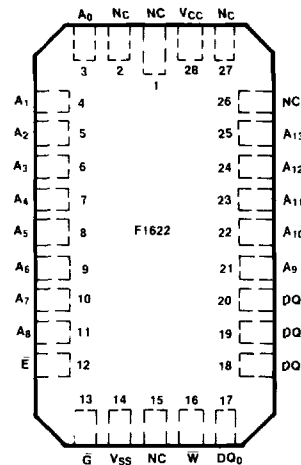


Connection Diagrams

24-Pin DIP (Top View)



28-Pin LCC (Top View)



F1622 LCC